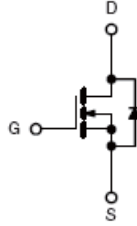


:95HI F9`

TrenchFET Power MOSFET

5DD@=7 5H-CBG`

- Load Switch for Portable Devices
- DC/DC Converter



9e i]jU`Ybh` 7]fWi]h`



AUI]a i a `fUh]b [g`flH_v1&)°C` i b`Ygg`ch\Yfk]gY`bchYXL`

| DUfU a YhYf` | Gma Vcl | JU` i Y | I b]h |
|--|-----------|-------------|-------|
| Drain-Source Voltage | V_{DS} | 20 | V |
| Gate-Source Voltage | V_{GS} | ± 8 | |
| Continuous Drain Current | I_D | $I \dot{E}$ | A |
| Continuous Source-Drain Current(Diode Conduction) | I_S | 0.6 | |
| Power Dissipation | P_D | 0.35 | W |
| Thermal Resistance from Junction to Ambient (tm5s) | R_{JA} | 357 | °C/W |
| Operating Junction | T_J | 150 | °C |
| Storage Temperature | T_{STG} | -55 ~+150 | |

Electrical characteristics (T_a=25°C unless otherwise noted)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Units |
|---|----------------------|--|-----|-------|------|-------|
| Static | | | | | | |
| Drain-source breakdown voltage | V _{(BR)DSS} | V _{GS} = 0V, I _D = 10μA | 20 | | | V |
| Gate-threshold voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 50μA | 0.1 | 0.95 | 1.2 | |
| Gate-body leakage | I _{GSS} | V _{DS} = 0V, V _{GS} = ±8V | | | ±100 | nA |
| Zero gate voltage drain current | I _{DSS} | V _{DS} = 20V, V _{GS} = 0V | | | 1 | μA |
| Drain-source on-resistance ^a | r _{DS(on)} | V _{GS} = 4.5V, I _D = 1.5A | | 0.06F | 0.06 | Ω |
| | | V _{GS} = 2.5V, I _D = 3.6A | | 0.06J | 0.06 | |
| Forward transconductance ^a | g _{fs} | V _{DS} = 5V, I _D = 3.6A | | 8 | | S |
| Diode forward voltage | V _{SD} | I _S = 0.94A, V _{GS} = 0V | | 0.76 | 1.2 | V |
| Dynamic | | | | | | |
| Total gate charge | Q _g | V _{DS} = 10V, V _{GS} = 4.5V, I _D = 3.6A | | 4.0 | | nC |
| Gate-source charge | Q _{gs} | | | 0.65 | | |
| Gate-drain charge | Q _{gd} | | | 1.5 | | |
| Input capacitance ^b | C _{iss} | V _{DS} = 10V, V _{GS} = 0V, f = 1MHz | | 300 | | pF |
| Output capacitance ^b | C _{oss} | | | 120 | | |
| Reverse transfer capacitance ^b | C _{rss} | | | 80 | | |
| Switching^b | | | | | | |
| Turn-on delay time | t _{d(on)} | V _{DD} = 10V, R _L = 5.5 Ω, I _D = 3.6A, V _{GEN} = 4.5V, R _g = 6Ω | | 7 | | ns |
| Rise time | t _r | | | 55 | | |
| Turn-off delay time | t _{d(off)} | | | 16 | | |
| Fall time | t _f | | | 10 | | |

Notes :

- Pulse Test : Pulse width 300μs, duty cycle 2%.
- These parameters have no way to verify.

Hmd]WU`7 \UfUWhYf]gh]Wg

